

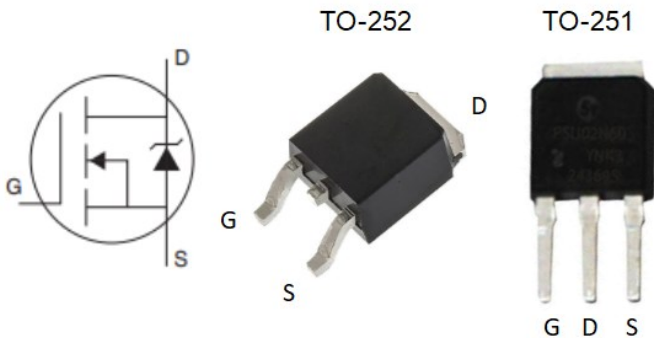
Description

The CM04N80U/D is the N-Channel enhancement mode power field effect transistors with high cell density, high voltage planar technology. This high density process and design have been optimized switching performance and especially tailored to minimize on-state resistance.

Features

- V_{DS} : 800V
- I_D (@ $V_{GS}=10V$): 3.7A
- $R_{DS(ON)}$ (@ $V_{GS}=10V$): < 3.7 Ω
- High density cell design for extremely low $R_{DS(ON)}$
- Excellent on-resistance and DC current capability

Equivalent Circuit and Pin Configuration



Applications

- AC/DC load switch
- SMPS
- Notebooks and Handhelds adapter
- UPS Power

Marking Information



X=Package type
 G=Halogen Free
 XXXX = Marking Code

Ordering Information

P/N	Package Type	Packaging	Remark
CM04N80U	TO-252	Tape and reel	ROHS
CM04N80UG	TO-252	Tape and reel	Halogen Free
CM04N80D	TO-251	Tube	ROHS
CM04N80DG	TO-251	Tube	Halogen Free

Absolute Maximum Ratings (Tc=25 °C unless otherwise noted)

Parameter	Symbol	Maximum	Unit
Drain-source Voltage	V_{DS}	800	V
Gate-source Voltage	V_{GS}	± 30	V
Continuous Drain Current ⁽¹⁾	I_D	$T_c=25^\circ C$	3.7 ⁽⁴⁾
		$T_c=100^\circ C$	3 ⁽⁴⁾
Pulsed Drain Current ⁽²⁾	I_{DM}	14.8 ⁽⁴⁾	A
Total Power Dissipation ⁽³⁾	$P_D @ T_c=25^\circ C$	100	W
	Derating Factor above 25°C	0.8	W/°C
Thermal Resistance Junction-to-Case ⁽³⁾	$R_{\theta JC}$	1.25	°C/W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (T_c=25 °C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	B _V D _{SS}	V _{GS} =0V, I _D =250μA	800			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =800V, V _{GS} =0V, T _C =25°C			2	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V
Static Drain-Source on-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =2A		3.1	3.7	Ω
Diode Forward Voltage	V _{SD}	I _S =3.7A, V _{GS} =0V			1.2	V
Maximum Body-Diode Continuous Current	I _S				3.7	A
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0V, f=1.0MHz		614		pF
Output Capacitance	C _{oss}			55		
Reverse Transfer Capacitance	C _{rss}			7		
Switching Parameters						
Total Gate Charge	Q _g	V _{DS} =640V, I _D =3.7A, V _{GS} =10V		21.5		nC
Gate Source Charge	Q _{gs}			2.9		
Gate Drain Charge	Q _{gd}			11.8		
Turn-on Delay Time	t _{D(on)}	V _{GS} =10V, V _{DD} =400V, I _D =3.7A, R _{GEN} =25Ω		16		ns
Turn-on Rise Time	t _r			44		
Turn-off Delay Time	t _{D(off)}			23		
Turn-off Fall Time	t _f			31		

Noted: (1) Pulse Test: Pulse Width ≤ 300us, Duty cycle ≤ 2%.

(2) Pulse width limited by maximum junction temperature

(3) Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch. With 2oz Copper, t ≤ 10s

(4) Drain current limited by maximum junction temperature

Typical Performance Characteristics

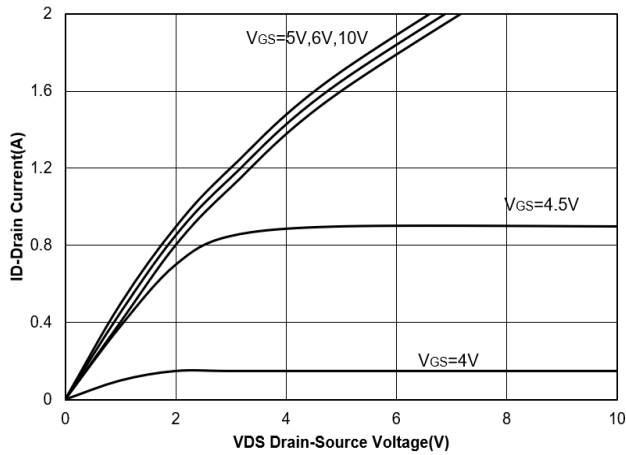


Figure 1. Output Characteristics

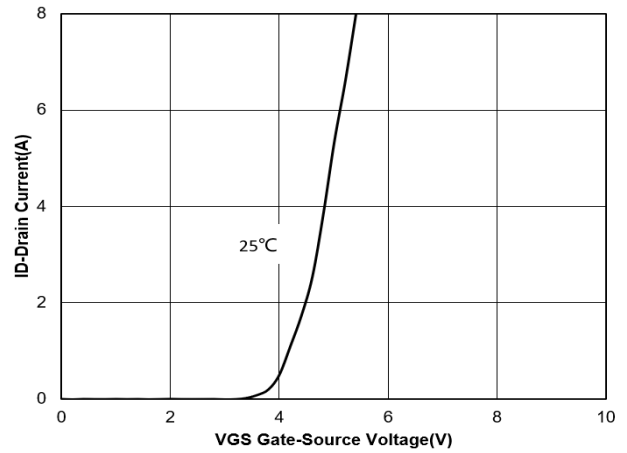


Figure 2. Transfer Characteristics

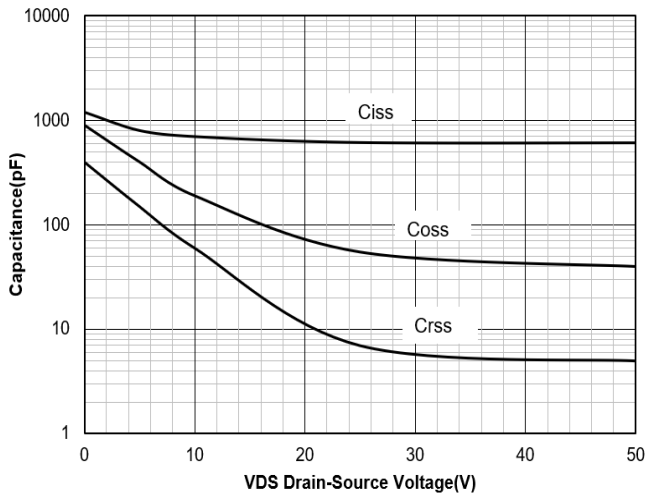


Figure 3. Capacitance Characteristics

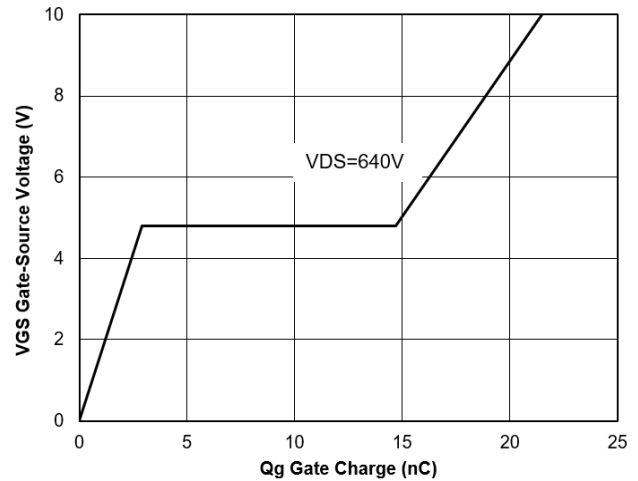


Figure 4. Gate Charge

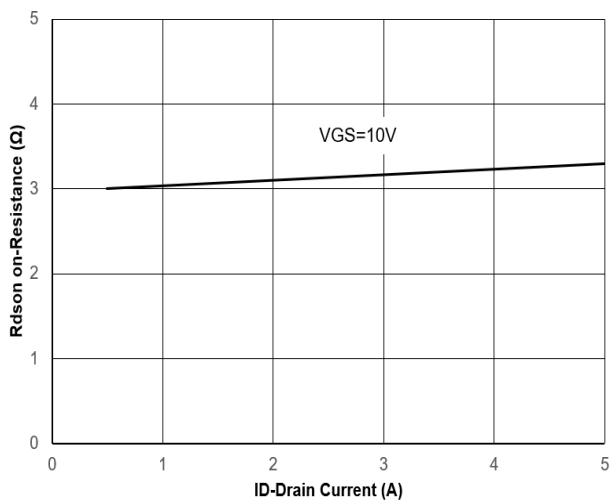


Figure 5. Drain-Source on Resistance

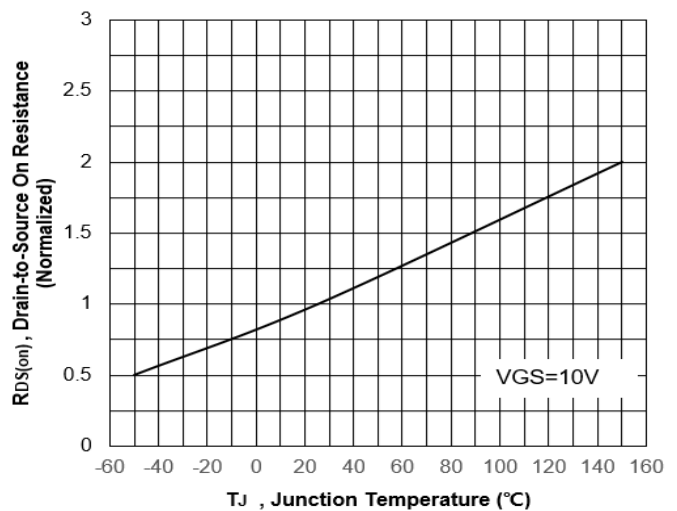


Figure 6. Normalized On-Resistance Vs. Temperature

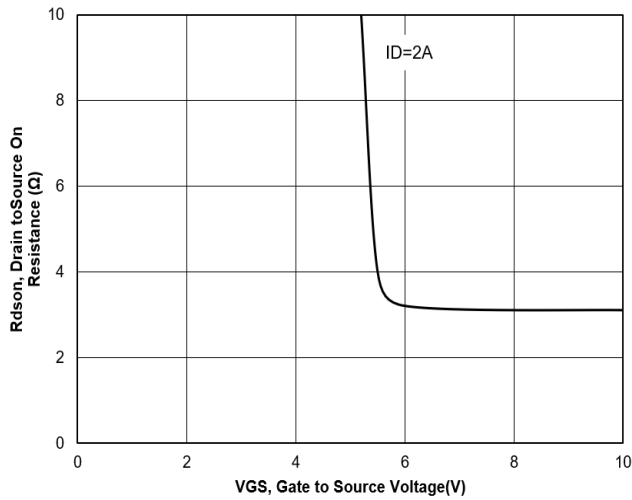


Figure 7. Typical Drain to Source ON Resistance VS Gate Voltage and Drain Current

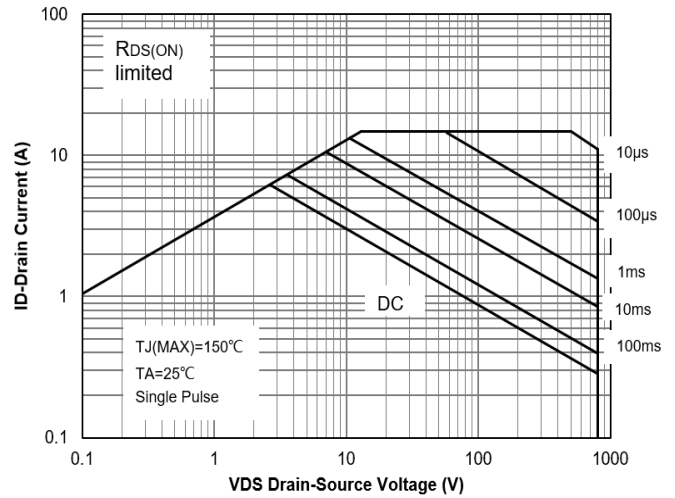


Figure 8. Safe Operation Area

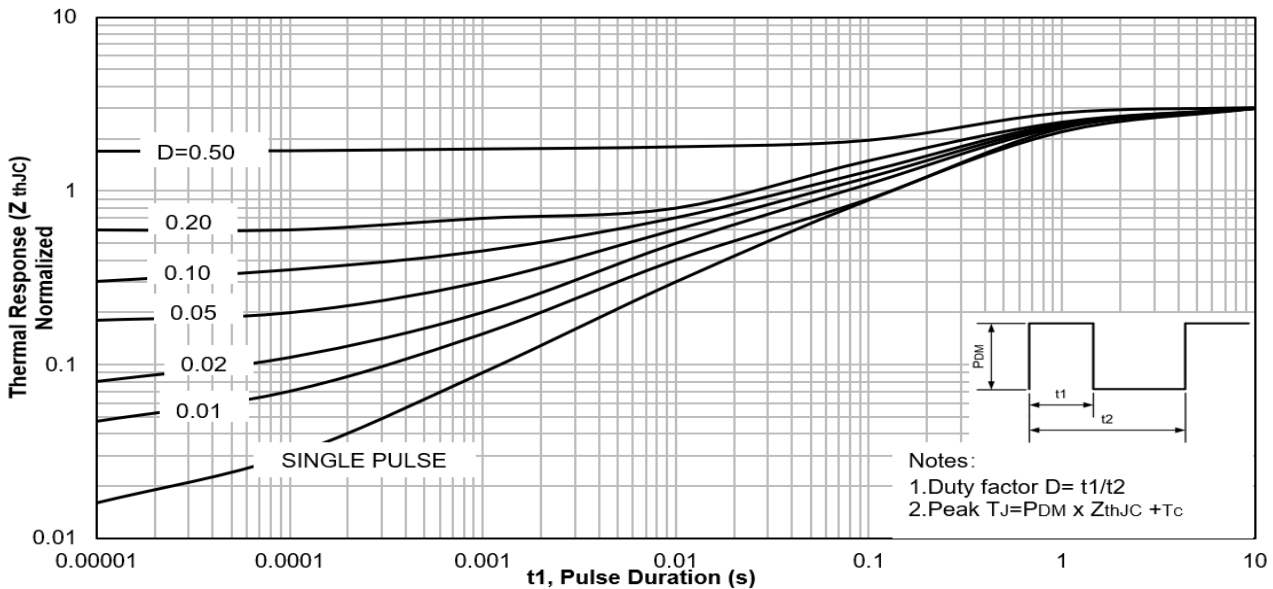


Figure 9. Maximum Effective Transient Thermal Impedance ,Junction-to-Case

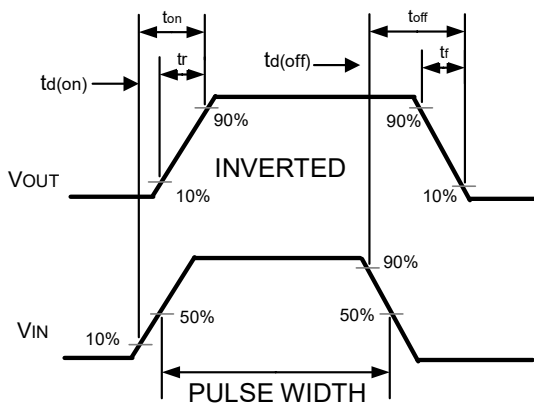
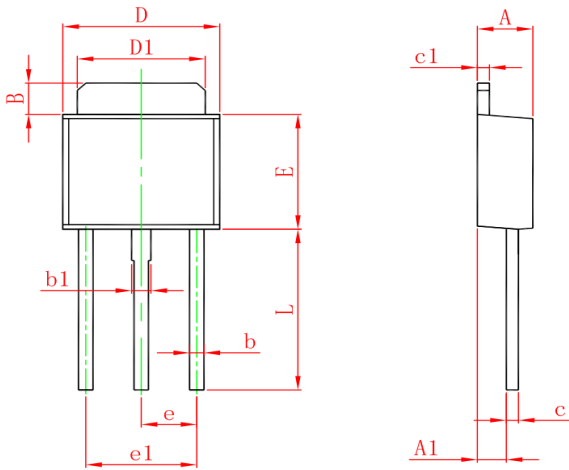


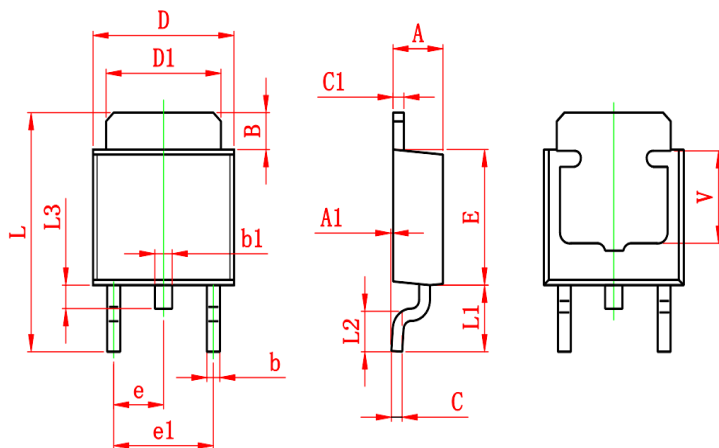
Figure 10. Switching wave

TO-251 Package Outline Drawing



Symbol	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	1.050	1.350	0.042	0.054
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
L	7.500	7.900	0.295	0.311

TO-252 Package Outline Drawing



Symbol	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
L	9.500	9.900	0.374	0.390
L1	2.550	2.900	0.100	0.114
L2	1.400	1.780	0.055	0.070
L3	0.600	0.900	0.024	0.035
V	3.800 REF.		0.150 REF.	

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